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"[Embedded - Microcontrollers](#)" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "[Embedded - Microcontrollers](#)"

Details

Product Status	Active
Core Processor	ARM® Cortex®-M3
Core Size	32-Bit Single-Core
Speed	120MHz
Connectivity	CANbus, I ² C, IrDA, LINbus, MMC, SPI, UART/USART, USB OTG
Peripherals	Brown-out Detect/Reset, DMA, I ² S, LCD, POR, PWM, WDT
Number of I/O	82
Program Memory Size	1MB (1M x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	132K x 8
Voltage - Supply (Vcc/Vdd)	1.8V ~ 3.6V
Data Converters	A/D 16x12b; D/A 2x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 105°C (TA)
Mounting Type	Surface Mount
Package / Case	100-LQFP
Supplier Device Package	100-LQFP (14x14)
Purchase URL	https://www.e-xfl.com/product-detail/stmicroelectronics/stm32f215vgt7

Table 1. Device summary

Reference	Part numbers
STM32F215xx	STM32F215RG, STM32F215VG, STM32F215ZG STM32F215RE, STM32F215VE, STM32F215ZE
STM32F217xx	STM32F217VG, STM32F217IG, STM32F217ZG STM32F217VE, STM32F217IE, STM32F217ZE

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3 Functional overview

3.1 ARM® Cortex®-M3 core with embedded Flash and SRAM

The ARM® Cortex®-M3 processor is the latest generation of ARM processors for embedded systems. It was developed to provide a low-cost platform that meets the needs of MCU implementation, with a reduced pin count and low-power consumption, while delivering outstanding computational performance and an advanced response to interrupts.

The ARM® Cortex®-M3 32-bit RISC processor features exceptional code-efficiency, delivering the high-performance expected from an ARM core in the memory size usually associated with 8- and 16-bit devices.

With its embedded ARM® core, the STM32F21x family is compatible with all ARM® tools and software.

Figure 4 shows the general block diagram of the STM32F21x family.

3.2 Adaptive real-time memory accelerator (ART Accelerator™)

The ART Accelerator™ is a memory accelerator which is optimized for STM32 industry-standard ARM® Cortex®-M3 processors. It balances the inherent performance advantage of the ARM® Cortex®-M3 over Flash memory technologies, which normally requires the processor to wait for the Flash memory at higher operating frequencies.

To release the processor full 150 DMIPS performance at this frequency, the accelerator implements an instruction prefetch queue and branch cache which increases program execution speed from the 128-bit Flash memory. Based on CoreMark® benchmark, the performance achieved thanks to the ART accelerator is equivalent to 0 wait state program execution from Flash memory at a CPU frequency up to 120 MHz.

3.3 Memory protection unit

The memory protection unit (MPU) is used to manage the CPU accesses to memory to prevent one task to accidentally corrupt the memory or resources used by any other active task. This memory area is organized into up to 8 protected areas that can in turn be divided up into 8 subareas. The protection area sizes are between 32 bytes and the whole 4 gigabytes of addressable memory.

The MPU is especially helpful for applications where some critical or certified code has to be protected against the misbehavior of other tasks. It is usually managed by an RTOS (real-time operating system). If a program accesses a memory location that is prohibited by the MPU, the RTOS can detect it and take action. In an RTOS environment, the kernel can dynamically update the MPU area setting, based on the process to be executed.

The MPU is optional and can be bypassed for applications that do not need it.

Table 7. STM32F21x pin and ball definitions (continued)

Pins					Pin name (function after reset) ⁽¹⁾	Pin type	I / O structure	Note	Alternate functions	Additional functions
LQFP64	LQFP100	LQFP144	LQFP176	UFBGA176						
-	-	-	85	M12	PH8	I/O	FT	-	I2C3_SDA, DCMI_HSYNC, EVENTOUT	-
-	-	-	86	M13	PH9	I/O	FT	-	I2C3_SMBA, TIM12_CH2, DCMI_D0, EVENTOUT	-
-	-	-	87	L13	PH10	I/O	FT	-	TIM5_CH1, DCMI_D1, EVENTOUT	-
-	-	-	88	L12	PH11	I/O	FT	-	TIM5_CH2, DCMI_D2, EVENTOUT	-
-	-	-	89	K12	PH12	I/O	FT	-	TIM5_CH3, DCMI_D3, EVENTOUT	-
-	-	-	90	H12	V _{SS}	S	-	-	-	-
-	-	-	91	J12	V _{DD}	S	-	-	-	-
33	51	73	92	P12	PB12	I/O	FT	-	SPI2_NSS, I2S2_WS, I2C2_SMBA, USART3_CK, TIM1_BKIN, CAN2_RX, OTG_HS_ULPI_D5, ETH_RMII_TXD0, ETH_MII_TXD0, OTG_HS_ID, EVENTOUT	-
34	52	74	93	P13	PB13	I/O	FT	-	SPI2_SCK, I2S2_SCK, USART3_CTS, TIM1_CH1N, CAN2_TX, OTG_HS_ULPI_D6, ETH_RMII_TXD1, ETH_MII_TXD1, EVENTOUT	OTG_HS_ VBUS
35	53	75	94	R14	PB14	I/O	FT	-	SPI2_MISO, TIM1_CH2N, TIM12_CH1, OTG_HS_DM, USART3_RTS, TIM8_CH2N, EVENTOUT	-
36	54	76	95	R15	PB15	I/O	FT	-	SPI2_MOSI, I2S2_SD, TIM1_CH3N, TIM8_CH3N, TIM12_CH2, OTG_HS_DP, RTC_50Hz, EVENTOUT	-
-	55	77	96	P15	PD8	I/O	FT	-	FSMC_D13, USART3_TX, EVENTOUT	-
-	56	78	97	P14	PD9	I/O	FT	-	FSMC_D14, USART3_RX, EVENTOUT	-

Table 7. STM32F21x pin and ball definitions (continued)

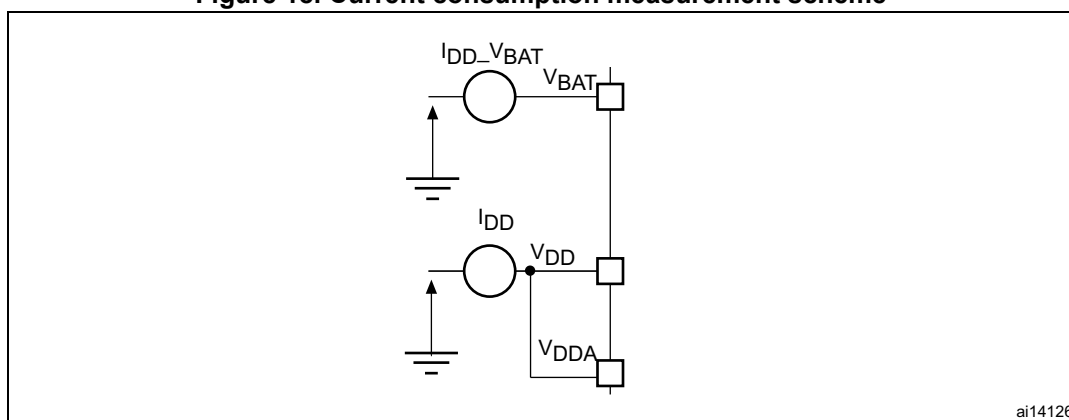
Pins					Pin name (function after reset) ⁽¹⁾	Pin type	I / O structure	Note	Alternate functions	Additional functions
LQFP64	LQFP100	LQFP144	LQFP176	UFBGA176						
54	83	116	144	D12	PD2	I/O	FT	-	TIM3_ETR, UART5_RX, SDIO_CMD, DCMI_D11, EVENTOUT	-
-	84	117	145	D11	PD3	I/O	FT	-	FSMC_CLK, USART2_CTS, EVENTOUT	-
-	85	118	146	D10	PD4	I/O	FT	-	FSMC_NOE, USART2_RTS, EVENTOUT	-
-	86	119	147	C11	PD5	I/O	FT	-	FSMC_NWE, USART2_TX, EVENTOUT	-
-	-	120	148	D8	V _{SS}	S		-	-	-
-	-	121	149	C8	V _{DD}	S		-	-	-
-	87	122	150	B11	PD6	I/O	FT	-	FSMC_NWAIT, USART2_RX, EVENTOUT	-
-	88	123	151	A11	PD7	I/O	FT	-	USART2_CK, FSMC_NE1, FSMC_NCE2, EVENTOUT	-
-	-	124	152	C10	PG9	I/O	FT	-	USART6_RX, FSMC_NE2, FSMC_NCE3, EVENTOUT	-
-	-	125	153	B10	PG10	I/O	FT	-	FSMC_NCE4_1, FSMC_NE3, EVENTOUT	-
-	-	126	154	B9	PG11	I/O	FT	-	FSMC_NCE4_2, ETH_MII_TX_EN, ETH_RMII_TX_EN, EVENTOUT	-
-	-	127	155	B8	PG12	I/O	FT	-	FSMC_NE4, USART6_RTS, EVENTOUT	-
-	-	128	156	A8	PG13	I/O	FT	-	FSMC_A24, USART6_CTS, ETH_MII_TXD0, ETH_RMII_TXD0, EVENTOUT	-
-	-	129	157	A7	PG14	I/O	FT	-	FSMC_A25, USART6_TX, ETH_MII_TXD1, ETH_RMII_TXD1, EVENTOUT	-
-	-	130	158	D7	V _{SS}	S	-	-	-	-
-	-	131	159	C7	V _{DD}	S	-	-	-	-

Table 9. Alternate function mapping (continued)

Port		AF0	AF1	AF2	AF3	AF4	AF5	AF6	AF7	AF8	AF9	AF10	AF11	AF12	AF13	AF014	AF15
		SYS	TIM1/2	TIM3/4/5	TIM8/9/10/11	I2C1/I2C2/I2C3	SPI1/SPI2/I2S2	SPI3/I2S3	USART1/2/3	UART4/5/ USART6	CAN1/CAN2/ TIM12/13/14	OTG_FS/ OTG_HS	ETH	FSMC/SDIO/ OTG_HS	DCMI		
Port D	PD0	-	-	-	-	-	-	-	-	-	CAN1_RX	-	-	FSMC_D2	-	-	EVENTOUT
	PD1	-	-	-	-	-	-	-	-	-	CAN1_TX	-	-	FSMC_D3	-	-	EVENTOUT
	PD2	-	-	TIM3_ETR	-	-	-	-	-	UART5_RX	-	-	-	SDIO_CMD	DCMI_D11	-	EVENTOUT
	PD3	-	-	-	-	-	-	-	USART2_CTS	-	-	-	-	FSMC_CLK	-	-	EVENTOUT
	PD4	-	-	-	-	-	-	-	USART2_RTS	-	-	-	-	FSMC_NOE	-	-	EVENTOUT
	PD5	-	-	-	-	-	-	-	USART2_TX	-	-	-	-	FSMC_NWE	-	-	EVENTOUT
	PD6	-	-	-	-	-	-	-	USART2_RX	-	-	-	-	FSMC_NWAIT	-	-	EVENTOUT
	PD7	-	-	-	-	-	-	-	USART2_CK	-	-	-	-	FSMC_NE1/ FSMC_NCE2	-	-	EVENTOUT
	PD8	-	-	-	-	-	-	-	USART3_TX	-	-	-	-	FSMC_D13	-	-	EVENTOUT
	PD9	-	-	-	-	-	-	-	USART3_RX	-	-	-	-	FSMC_D14	-	-	EVENTOUT
	PD10	-	-	-	-	-	-	-	USART3_CK	-	-	-	-	FSMC_D15	-	-	EVENTOUT
	PD11	-	-	-	-	-	-	-	USART3_CTS	-	-	-	-	FSMC_A16	-	-	EVENTOUT
	PD12	-	-	TIM4_CH1	-	-	-	-	USART3_RTS	-	-	-	-	FSMC_A17	-	-	EVENTOUT
	PD13	-	-	TIM4_CH2	-	-	-	-	-	-	-	-	-	FSMC_A18	-	-	EVENTOUT
	PD14	-	-	TIM4_CH3	-	-	-	-	-	-	-	-	-	FSMC_D0	-	-	EVENTOUT
	PD15	-	-	TIM4_CH4	-	-	-	-	-	-	-	-	-	FSMC_D1	-	-	EVENTOUT
Port E	PE0	-	-	TIM4_ETR	-	-	-	-	-	-	-	-	-	FSMC_NBL0	DCMI_D2	-	EVENTOUT
	PE1	-	-	-	-	-	-	-	-	-	-	-	-	FSMC_NBL1	DCMI_D3	-	EVENTOUT
	PE2	TRACECLK	-	-	-	-	-	-	-	-	-	-	ETH_MII_TXD3	FSMC_A23	-	-	EVENTOUT
	PE3	TRACED0	-	-	-	-	-	-	-	-	-	-	-	FSMC_A19	-	-	EVENTOUT
	PE4	TRACED1	-	-	-	-	-	-	-	-	-	-	-	FSMC_A20	DCMI_D4	-	EVENTOUT
	PE5	TRACED2	-	-	TIM9_CH1	-	-	-	-	-	-	-	-	FSMC_A21	DCMI_D6	-	EVENTOUT
	PE6	TRACED3	-	-	TIM9_CH2	-	-	-	-	-	-	-	-	FSMC_A22	DCMI_D7	-	EVENTOUT
	PE7	-	TIM1_ETR	-	-	-	-	-	-	-	-	-	-	FSMC_D4	-	-	EVENTOUT
	PE8	-	TIM1_CH1N	-	-	-	-	-	-	-	-	-	-	FSMC_D5	-	-	EVENTOUT
	PE9	-	TIM1_CH1	-	-	-	-	-	-	-	-	-	-	FSMC_D6	-	-	EVENTOUT
	PE10	-	TIM1_CH2N	-	-	-	-	-	-	-	-	-	-	FSMC_D7	-	-	EVENTOUT
	PE11	-	TIM1_CH2	-	-	-	-	-	-	-	-	-	-	FSMC_D8	-	-	EVENTOUT
	PE12	-	TIM1_CH3N	-	-	-	-	-	-	-	-	-	-	FSMC_D9	-	-	EVENTOUT
	PE13	-	TIM1_CH3	-	-	-	-	-	-	-	-	-	-	FSMC_D10	-	-	EVENTOUT
	PE14	-	TIM1_CH4	-	-	-	-	-	-	-	-	-	-	FSMC_D11	-	-	EVENTOUT
	PE15	-	TIM1_BKIN	-	-	-	-	-	-	-	-	-	-	FSMC_D12	-	-	EVENTOUT

6.1.7 Current consumption measurement

Figure 18. Current consumption measurement scheme



6.2 Absolute maximum ratings

Stresses above the absolute maximum ratings listed in [Table 10: Voltage characteristics](#), [Table 11: Current characteristics](#), and [Table 12: Thermal characteristics](#) may cause permanent damage to the device. These are stress ratings only and functional operation of the device at these conditions is not implied. Exposure to maximum rating conditions for extended periods may affect device reliability.

Table 10. Voltage characteristics

Symbol	Ratings	Min	Max	Unit
$V_{DD}-V_{SS}$	External main supply voltage (including V_{DDA} , V_{DD}) ⁽¹⁾	-0.3	4.0	V
V_{IN}	Input voltage on five-volt tolerant pin ⁽²⁾	$V_{SS}-0.3$	$V_{DD}+4$	
	Input voltage on any other pin	$V_{SS}-0.3$	4.0	
$ \Delta V_{DDx} $	Variations between different V_{DD} power pins	-	50	mV
$ V_{SSx}-V_{SS} $	Variations between all the different ground pins	-	50	
$V_{ESD(HBM)}$	Electrostatic discharge voltage (human body model)	see Section 6.3.14: Absolute maximum ratings (electrical sensitivity)		-

1. All main power (V_{DD} , V_{DDA}) and ground (V_{SS} , V_{SSA}) pins must always be connected to the external power supply, in the permitted range.
2. V_{IN} maximum value must always be respected. Refer to [Table 11](#) for the values of the maximum allowed injected current.

Table 25. Peripheral current consumption (continued)

Peripheral ⁽¹⁾		Typical consumption at 25 °C	Unit
APB1	TIM2	0.61	mA
	TIM3	0.49	
	TIM4	0.54	
	TIM5	0.62	
	TIM6	0.20	
	TIM7	0.20	
	TIM12	0.36	
	TIM13	0.28	
	TIM14	0.25	
	USART2	0.25	
	USART3	0.25	
	UART4	0.25	
	UART5	0.26	
	I2C1	0.25	
	I2C2	0.25	
	I2C3	0.25	
	SPI2	0.20/0.10	
	SPI3	0.18/0.09	
	CAN1	0.31	
	CAN2	0.30	
	DAC channel 1 ⁽²⁾	1.11	
	DAC channel 1 ⁽³⁾	1.11	
	PWR	0.15	
	WWDG	0.15	

6.3.11 PLL spread spectrum clock generation (SSCG) characteristics

The spread spectrum clock generation (SSCG) feature allows to reduce electromagnetic interferences (see [Table 41: EMI characteristics](#)). It is available only on the main PLL.

Table 35. SSCG parameters constraint

Symbol	Parameter	Min	Typ	Max ⁽¹⁾	Unit
f_{Mod}	Modulation frequency	-	-	10	KHz
md	Peak modulation depth	0.25	-	2	%
MODEPER * INCSTEP	-	-	-	$2^{15}-1$	-

1. Guaranteed by design, not tested in production.

Equation 1

The frequency modulation period (MODEPER) is given by the equation below:

$$MODEPER = \text{round}[f_{PLL_IN} / (4 \times f_{Mod})]$$

f_{PLL_IN} and f_{Mod} must be expressed in Hz.

As an example:

If $f_{PLL_IN} = 1$ MHz and $f_{MOD} = 1$ kHz, the modulation depth (MODEPER) is given by equation 1:

$$MODEPER = \text{round}[10^6 / (4 \times 10^3)] = 250$$

Equation 2

Equation 2 allows to calculate the increment step (INCSTEP):

$$INCSTEP = \text{round}[(2^{15} - 1) \times md \times PLLN] / (100 \times 5 \times MODEPER)$$

f_{VCO_OUT} must be expressed in MHz.

With a modulation depth (md) = ± 2 % (4 % peak to peak), and PLLN = 240 (in MHz):

$$INCSTEP = \text{round}[(2^{15} - 1) \times 2 \times 240] / (100 \times 5 \times 250) = 126md(\text{quantitized})\%$$

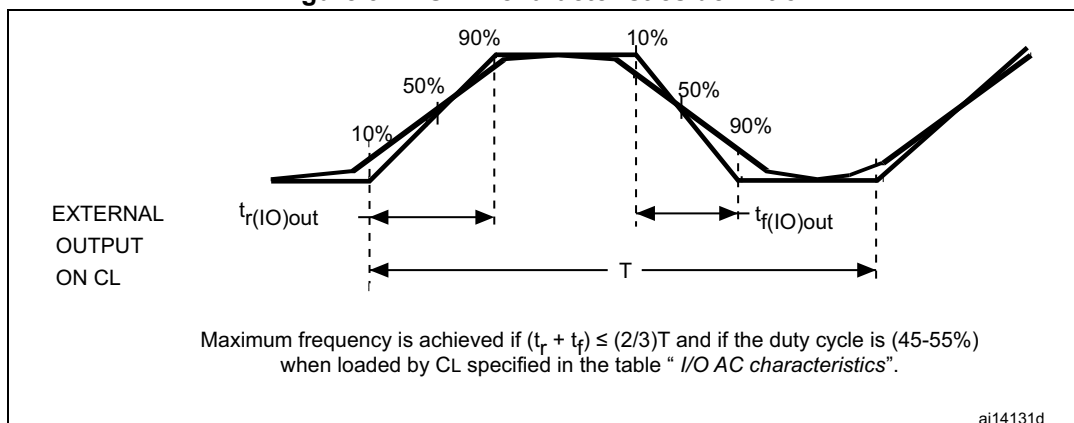
An amplitude quantization error may be generated because the linear modulation profile is obtained by taking the quantized values (rounded to the nearest integer) of MODEPER and INCSTEP. As a result, the achieved modulation depth is quantized. The percentage quantized modulation depth is given by the following formula:

$$md_{\text{quantized}}\% = (MODEPER \times INCSTEP \times 100 \times 5) / ((2^{15} - 1) \times PLLN)$$

As a result:

$$md_{\text{quantized}}\% = (250 \times 126 \times 100 \times 5) / ((2^{15} - 1) \times 240) = 2.0002\%(\text{peak})$$

Figure 37. I/O AC characteristics definition



6.3.17 NRST pin characteristics

The NRST pin input driver uses CMOS technology. It is connected to a permanent pull-up resistor, R_{PU} (see [Table 48](#)).

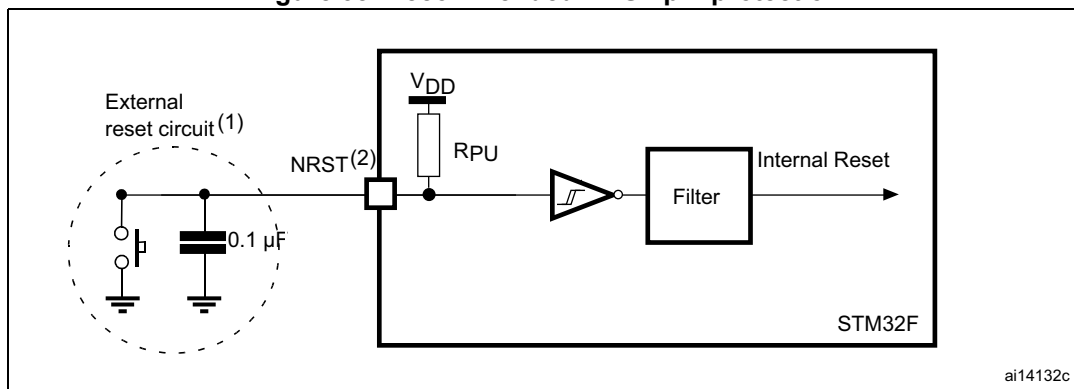
Unless otherwise specified, the parameters given in [Table 48](#) are derived from tests performed under the ambient temperature and V_{DD} supply voltage conditions summarized in [Table 13](#).

Table 48. NRST pin characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
R_{PU}	Weak pull-up equivalent resistor ⁽¹⁾	$V_{IN} = V_{SS}$	30	40	50	$k\Omega$
$V_{F(NRST)}^{(2)}$	NRST Input filtered pulse	-	-	-	100	ns
$V_{NF(NRST)}^{(2)}$	NRST Input not filtered pulse	$V_{DD} > 2.7 V$	300	-	-	ns
T_{NRST_OUT}	Generated reset pulse duration	Internal Reset source	20	-	-	μs

1. The pull-up is designed with a true resistance in series with a switchable PMOS. This PMOS contribution to the series resistance must be minimum (~10% order).
2. Guaranteed by design, not tested in production.

Figure 38. Recommended NRST pin protection



1. The reset network protects the device against parasitic resets.
2. The user must ensure that the level on the NRST pin can go below the $V_{IL(NRST)}$ max level specified in [Table 48](#). Otherwise the reset is not taken into account by the device.

6.3.18 TIM timer characteristics

The parameters given in [Table 49](#) and [Table 50](#) are guaranteed by design.

Refer to [Section 6.3.16: I/O port characteristics](#) for details on the input/output alternate function characteristics (output compare, input capture, external clock, PWM output).

Table 49. Characteristics of TIMx connected to the APB1 domain⁽¹⁾

Symbol	Parameter	Conditions	Min	Max	Unit
$t_{\text{res(TIM)}}$	Timer resolution time	AHB/APB1 prescaler distinct from 1, $f_{\text{TIMxCLK}} = 60 \text{ MHz}$	1	-	t_{TIMxCLK}
			16.7	-	ns
		AHB/APB1 prescaler = 1, $f_{\text{TIMxCLK}} = 30 \text{ MHz}$	1	-	t_{TIMxCLK}
			33.3	-	ns
f_{EXT}	Timer external clock frequency on CH1 to CH4	$f_{\text{TIMxCLK}} = 60 \text{ MHz}$ APB1= 30 MHz	0	$f_{\text{TIMxCLK}}/2$	MHz
			0	30	MHz
Res_{TIM}	Timer resolution		-	16/32	bit
t_{COUNTER}	16-bit counter clock period when internal clock is selected		1	65536	t_{TIMxCLK}
			0.0167	1092	μs
	32-bit counter clock period when internal clock is selected		1	-	t_{TIMxCLK}
			0.0167	71582788	μs
$t_{\text{MAX_COUNT}}$	Maximum possible count		-	65536×65536	t_{TIMxCLK}
			-	71.6	s

1. TIMx is used as a general term to refer to the TIM2, TIM3, TIM4, TIM5, TIM6, TIM7, and TIM12 timers.

I²S - SPI interface characteristics

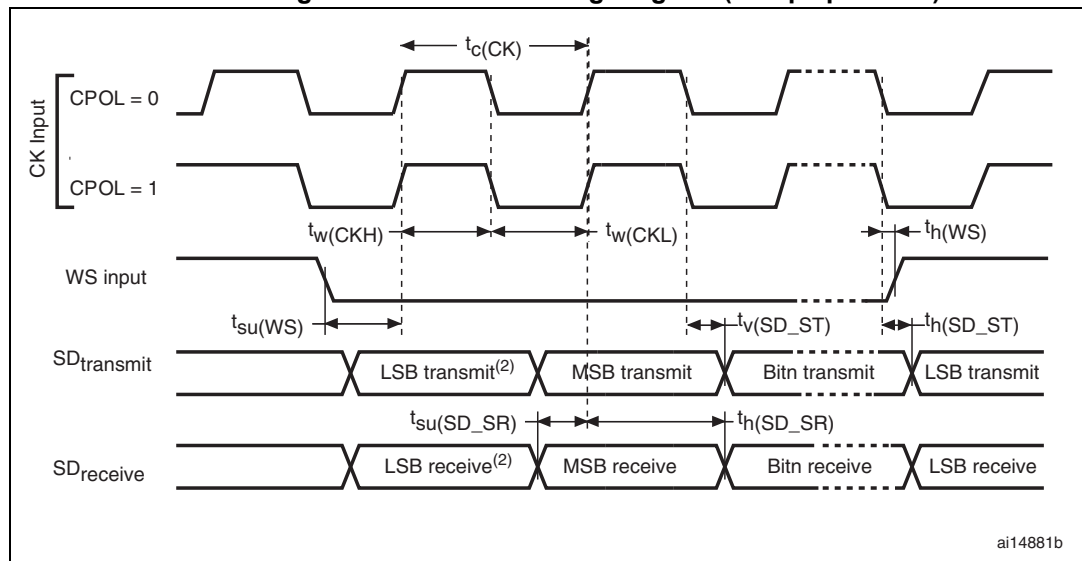
Unless otherwise specified, the parameters given in [Table 53](#) for SPI or in [Table 54](#) for I²S are derived from tests performed under the ambient temperature, f_{PCLKx} frequency and V_{DD} supply voltage conditions summarized in [Table 13](#).

Refer to [Section 6.3.16: I/O port characteristics](#) for more details on the input/output alternate function characteristics (NSS, SCK, MOSI, MISO for SPI and WS, CK, SD for I²S).

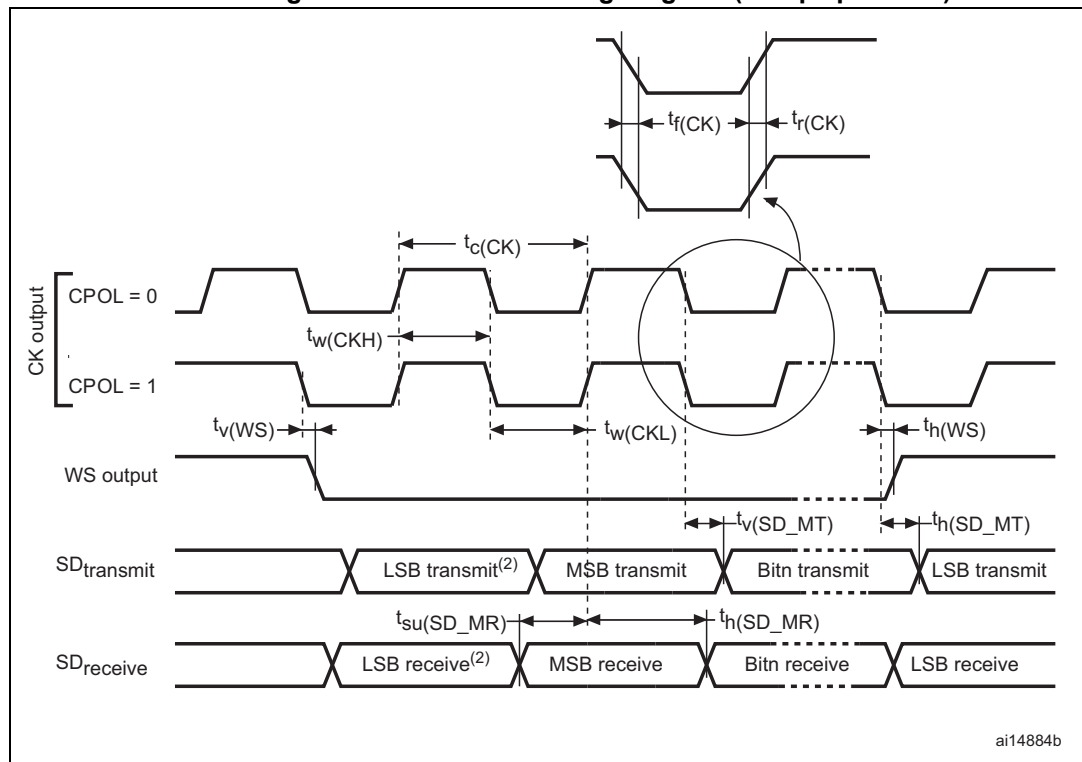
Table 53. SPI characteristics

Symbol	Parameter	Conditions	Min	Max	Unit
f_{SCK} $1/t_{c(SCK)}$	SPI clock frequency	SPI1 master/slave mode	-	30	MHz
		SPI2/SPI3 master/slave mode	-	15	
$t_{r(SCL)}$ $t_{f(SCL)}$	SPI clock rise and fall time	Capacitive load: $C = 30$ pF, $f_{PCLK} = 30$ MHz	-	8	ns
DuCy(SCK)	SPI slave input clock duty cycle	Slave mode	30	70	%
$t_{su(NSS)}^{(1)}$	NSS setup time	Slave mode	$4t_{PCLK}$	-	ns
$t_{h(NSS)}^{(1)}$	NSS hold time	Slave mode	$2t_{PCLK}$	-	
$t_{w(SCLH)}^{(1)}$ $t_{w(SCLL)}^{(1)}$	SCK high and low time	Master mode, $f_{PCLK} = 30$ MHz, presc = 2	$t_{PCLK}-3$	$t_{PCLK}+3$	
$t_{su(MI)}^{(1)}$ $t_{su(SI)}^{(1)}$	Data input setup time	Master mode	5	-	
		Slave mode	5	-	
$t_{h(MI)}^{(1)}$ $t_{h(SI)}^{(1)}$	Data input hold time	Master mode	5	-	
		Slave mode	4	-	
$t_{a(SO)}^{(1)(2)}$	Data output access time	Slave mode, $f_{PCLK} = 30$ MHz	0	$3t_{PCLK}$	
$t_{dis(SO)}^{(1)(3)}$	Data output disable time	Slave mode	2	10	
$t_{v(SO)}^{(1)}$	Data output valid time	Slave mode (after enable edge)	-	25	
$t_{v(MO)}^{(1)}$	Data output valid time	Master mode (after enable edge)	-	5	
$t_{h(SO)}^{(1)}$ $t_{h(MO)}^{(1)}$	Data output hold time	Slave mode (after enable edge)	15	-	
		Master mode (after enable edge)	2	-	

1. Guaranteed by characterization results, not tested in production.
2. Min time is for the minimum time to drive the output and the max time is for the maximum time to validate the data.
3. Min time is for the minimum time to invalidate the output and the max time is for the maximum time to put the data in Hi-Z

Figure 43. I²S slave timing diagram (Philips protocol)⁽¹⁾

1. LSB transmit/receive of the previously transmitted byte. No LSB transmit/receive is sent before the first byte.

Figure 44. I²S master timing diagram (Philips protocol)⁽¹⁾

1. Guaranteed by characterization results, not tested in production.
2. LSB transmit/receive of the previously transmitted byte. No LSB transmit/receive is sent before the first byte.

USB OTG FS characteristics

The USB OTG interface is USB-IF certified (Full-Speed). This interface is present in both the USB OTG HS and USB OTG FS controllers.

Table 55. USB OTG FS startup time

Symbol	Parameter	Max	Unit
$t_{\text{STARTUP}}^{(1)}$	USB OTG FS transceiver startup time	1	μs

1. Guaranteed by design, not tested in production.

Table 56. USB OTG FS DC electrical characteristics

Symbol	Parameter	Conditions	Min ⁽¹⁾	Typ	Max ⁽¹⁾	Unit
Input levels	V_{DD}	USB OTG FS operating voltage	3.0 ⁽²⁾	-	3.6	V
	$V_{\text{DI}}^{(3)}$	Differential input sensitivity	I(USB_FS_DP/DM, USB_HS_DP/DM)	-	-	V
	$V_{\text{CM}}^{(3)}$	Differential common mode range	Includes V_{DI} range	-	2.5	
	$V_{\text{SE}}^{(3)}$	Single ended receiver threshold		-	2.0	
Output levels	V_{OL}	Static output level low	R_{L} of 1.5 k Ω to 3.6 V ⁽⁴⁾	-	0.3	V
	V_{OH}	Static output level high	R_{L} of 15 k Ω to $V_{\text{SS}}^{(4)}$	-	3.6	
R_{PD}	PA11, PA12, PB14, PB15 (USB_FS_DP/DM, USB_HS_DP/DM)	$V_{\text{IN}} = V_{\text{DD}}$	17	21	24	k Ω
	PA9, PB13 (OTG_FS_VBUS, OTG_HS_VBUS)		0.65	1.1	2.0	
R_{PU}	PA12, PB15 (USB_FS_DP, USB_HS_DP)	$V_{\text{IN}} = V_{\text{SS}}$	1.5	1.8	2.1	
	PA9, PB13 (OTG_FS_VBUS, OTG_HS_VBUS)	$V_{\text{IN}} = V_{\text{SS}}$	0.25	0.37	0.55	

1. All the voltages are measured from the local ground potential.
2. The STM32F215xx and STM32F217xx USB OTG FS functionality is ensured down to 2.7 V but not the full USB OTG FS electrical characteristics which are degraded in the 2.7-to-3.0 V V_{DD} voltage range.
3. Guaranteed by design, not tested in production.
4. R_{L} is the load connected on the USB OTG FS drivers

Table 80. Switching characteristics for PC Card/CF read and write cycles in I/O space⁽¹⁾⁽²⁾

Symbol	Parameter	Min	Max	Unit
$t_{w(NIOWR)}$	FSMC_NIOWR low width	$8T_{HCLK} - 0.5$	-	ns
$t_{v(NIOWR-D)}$	FSMC_NIOWR low to FSMC_D[15:0] valid	-	$5T_{HCLK} - 1$	ns
$t_{h(NIOWR-D)}$	FSMC_NIOWR high to FSMC_D[15:0] invalid	$8T_{HCLK} - 3$	-	ns
$t_{d(NCE4_1-NIOWR)}$	FSMC_NCE4_1 low to FSMC_NIOWR valid	-	$5T_{HCLK} + 1.5$	ns
$t_{h(NCEx-NIOWR)}$	FSMC_NCEx high to FSMC_NIOWR invalid	$5T_{HCLK}$	-	ns
$t_{d(NIORD-NCEx)}$	FSMC_NCEx low to FSMC_NIORD valid	-	$5T_{HCLK} + 1$	ns
$t_{h(NCEx-NIORD)}$	FSMC_NCEx high to FSMC_NIORD valid	$5T_{HCLK} - 0.5$	-	ns
$t_{w(NIORD)}$	FSMC_NIORD low width	$8T_{HCLK} + 1$	-	ns
$t_{su(D-NIORD)}$	FSMC_D[15:0] valid before FSMC_NIORD high	9.5	-	ns
$t_{d(NIORD-D)}$	FSMC_D[15:0] valid after FSMC_NIORD high	0	-	ns

1. $C_L = 30$ pF.

2. Guaranteed by characterization results, not tested in production.

NAND controller waveforms and timings

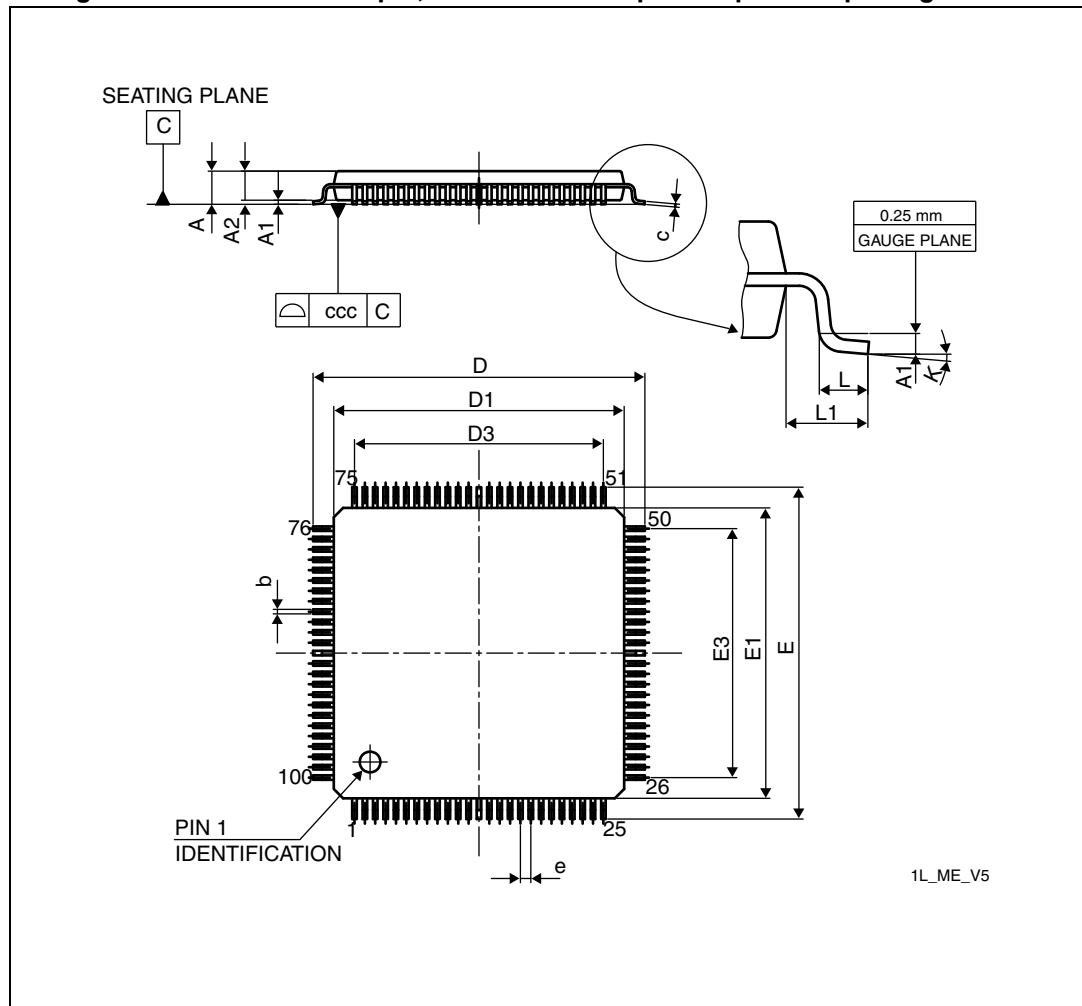
[Figure 69](#) through [Figure 72](#) represent synchronous waveforms, together with [Table 81](#) and [Table 82](#) provides the corresponding timings. The results shown in this table are obtained with the following FSMC configuration:

- COM.FSMC_SetupTime = 0x01;
- COM.FSMC_WaitSetupTime = 0x03;
- COM.FSMC_HoldSetupTime = 0x02;
- COM.FSMC_HiZSetupTime = 0x01;
- ATT.FSMC_SetupTime = 0x01;
- ATT.FSMC_WaitSetupTime = 0x03;
- ATT.FSMC_HoldSetupTime = 0x02;
- ATT.FSMC_HiZSetupTime = 0x01;
- Bank = FSMC_Bank_NAND;
- MemoryDataWidth = FSMC_MemoryDataWidth_16b;
- ECC = FSMC_ECC_Enable;
- ECCPageSize = FSMC_ECCPageSize_512Bytes;
- TCLRSetupTime = 0;
- TARSetupTime = 0;

In all timing tables, the T_{HCLK} is the HCLK clock period.

7.2 LQFP100 package information

Figure 77. LQFP100 - 100-pin, 14 x 14 mm low-profile quad flat package outline



1. Drawing is not to scale.

Table 87. LQFP100 - 100-pin, 14 x 14 mm low-profile quad flat package mechanical data

Symbol	millimeters			inches ⁽¹⁾		
	Min	Typ	Max	Min	Typ	Max
A	-	-	1.600	-	-	0.0630
A1	0.050	-	0.150	0.0020	-	0.0059
A2	1.350	1.400	1.450	0.0531	0.0551	0.0571
b	0.170	0.220	0.270	0.0067	0.0087	0.0106
c	0.090	-	0.200	0.0035	-	0.0079
D	15.800	16.000	16.200	0.6220	0.6299	0.6378
D1	13.800	14.000	14.200	0.5433	0.5512	0.5591

Table 90. UFBGA176+25, - 201-ball, 10 x 10 mm, 0.65 mm pitch, ultra fine pitch ball grid array package mechanical data (continued)

Symbol	millimeters			inches ⁽¹⁾		
	Min	Typ	Max	Min	Typ	Max
eee	-	-	0.150	-	-	0.0059
fff	-	-	0.050	-	-	0.0020

1. Values in inches are converted from mm and rounded to 4 decimal digits.

Figure 86. UFBGA176+25 - 201-ball, 10 x 10 mm, 0.65 mm pitch, ultra fine pitch ball grid array package recommended footprint

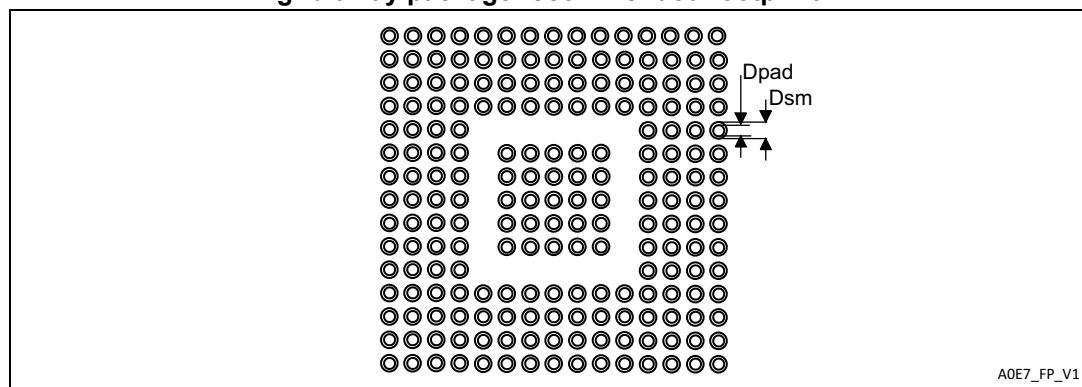


Table 91. UFBGA176+25 recommended PCB design rules (0.65 mm pitch BGA)

Dimension	Recommended values
Pitch	0.65 mm
Dpad	0.300 mm
Dsm	0.400 mm typ (depends on the soldermask registration tolerance)
Stencil opening	0.300 mm
Stencil thickness	Between 0.100 mm and 0.125 mm
Pad trace width	0.100 mm

Table 94. Document revision history (continued)

Date	Revision	Changes
25-Nov-2010	3	Added WLCSP66 (64+2) package. Added note 1 related to LQFP176 on cover page. Update I/Os in Section : Features. Updated Table 5: Multi-AHB matrix. Added case of BOR inactivation using IRROFF on WLCSP devices in Section 3.15: Power supply supervisor. Reworked Section 3.16: Voltage regulator to clarify regulator off modes. Added Section 3.19: VBAT operation. Modified V_{DD_3} pin in Table 7: STM32F21x pin and ball definitions, and added note related to the FSMC_NL pin. Renamed BYPASS-REG REGOFF, and add IRROFF pin. Changed V_{SS_SA} to V_{SS}, and V_{DD_SA} pin reserved for future use. Updated maximum HSE crystal frequency to 26 MHz. USART4/5 renamed UART4/5. USART4 pins renamed UART4 in Table 7: STM32F21x pin and ball definitions. Updated LIN and IrDA features for UART4/5 in Table 5: USART feature comparison. Section 6.2: Absolute maximum ratings: Updated V_{IN} minimum and maximum values and note for non-five-volt tolerant pins in Table 10: Voltage characteristics. Updated I_{INJ(PIN)} maximum values and related notes in Table 11: Current characteristics. Updated V_{DDA} minimum value in Table 13: General operating conditions. Added Note 2 and updated Maximum CPU frequency in Table 14: Limitations depending on the operating power supply range; and added Figure 19: Number of wait states versus fCPU and VDD range. Renamed Brownout Low, medium and High reset thresholds, Renamed V_{BORL}/V_{BORM}/V_{BORH}, V_{BOR1}/V_{BOR2}/V_{BOR3} in Table 18: Embedded reset and power control block characteristics. Changed f_{LSI} typical value in Table 32: LSI oscillator characteristics. Added Figure 33: ACCLSI versus temperature. Changed f_{OSC_IN} maximum value in Table 29: HSE 4-26 MHz oscillator characteristics. Changed f_{PLL_IN} maximum value in Table 33: Main PLL characteristics, and updated jitter parameters in Table 34: PLLI2S (audio PLL) characteristics. Section 6.3.16: I/O port characteristics: updated V_{IH} and V_{IL} in Table 45: I/O static characteristics. Added Note 1 below Table 46: Output voltage characteristics. Updated R_{PD} and R_{PU} parameter description in Table 56: USB OTG FS DC electrical characteristics. Updated V_{REF+} minimum value in Table 65: ADC characteristics. Updated Table 70: Embedded internal reference voltage. Removed Ethernet and USB2 for 64-pin devices in Table 93: Main applications versus package for STM32F2xxx microcontrollers. Added A.2: USB OTG full speed (FS) interface solutions, removed “OTG FS connection with external PHY” figure, updated Figure 85, Figure 86, and Figure 87 to add STULPI01B.

Table 94. Document revision history (continued)

Date	Revision	Changes
29-Oct-2012	8	Removed Figure 4. Compatible board design between STM32F10xx and STM32F2xx for LQFP176 package. Updated number of AHB buses in Section 2: Description and Section 3.12: Clocks and startup. Updated Note 2 below Figure 4: STM32F21x block diagram. Changed System memory to System memory + OTP in Figure 14: Memory map. Added Note 1 below Table 15: VCAP1/VCAP2 operating conditions. Updated V_{DDA} and V_{REF+} decoupling capacitor in Figure 17: Power supply scheme and updated Note 3. Changed simplex mode into half-duplex mode in Section 3.24: Inter-integrated sound (I2S). Replaced DAC1_OUT and DAC2_OUT by DAC_OUT1 and DAC_OUT2, respectively. Changed TIM2_CH1/TIM2_ETR into TIM2_CH1_ETR for PA0 and PA5 in Table 9: Alternate function mapping. Updated note applying to I_{DD} (external clock and all peripheral disabled) in Table 20: Typical and maximum current consumption in Run mode, code with data processing running from Flash memory (ART accelerator disabled). Updated Note 3 below Table 21: Typical and maximum current consumption in Sleep mode. Removed f_{HSE_ext} typical value in Table 27: High-speed external user clock characteristics. Updated master I2S clock jitter conditions and values in Table 34: PLLI2S (audio PLL) characteristics. Updated equations in Section 6.3.11: PLL spread spectrum clock generation (SSCG) characteristics. Swapped TTL and CMOS port conditions for V_{OL} and V_{OH} in Table 46: Output voltage characteristics. Updated $V_{IL(NRST)}$ and $V_{IH(NRST)}$ in Table 48: NRST pin characteristics. Updated Table 53: SPI characteristics and Table 54: I2S characteristics. Removed note 1 related to measurement points below Figure 41: SPI timing diagram - slave mode and CPHA = 1, Figure 42: SPI timing diagram - master mode, and Figure 43: I2S slave timing diagram (Philips protocol)(1). Updated t_{HC} in Table 60: ULPI timing. Updated Figure 47: Ethernet SMI timing diagram, Table 62: Dynamics characteristics: Ethernet MAC signals for SMI and Table 63: Dynamics characteristics: Ethernet MAC signals for RMII. Update f_{TRIG} in Table 65: ADC characteristics. Updated I_{DDA} description in Table 67: DAC characteristics. Updated note below Figure 52: Power supply and reference decoupling (VREF+ not connected to VDDA) and Figure 53: Power supply and reference decoupling (VREF+ connected to VDDA). Replaced $t_{d(CLKL-NOEL)}$ by $t_{d(CLKH-NOEL)}$ in Table 75: Synchronous multiplexed NOR/PSRAM read timings, Table 77: Synchronous non-multiplexed NOR/PSRAM read timings, Figure 59: Synchronous multiplexed NOR/PSRAM read timings and Figure 61: Synchronous non-multiplexed NOR/PSRAM read timings.